Features

- Single-voltage Operation
 - 5V Read
 - 5V Reprogramming
- Fast Read Access Time 55 ns
- Internal Program Control and Timer
- 16-Kbyte Boot Block with Lockout
- Fast Erase Cycle Time 10 seconds
- Byte-by-byte Programming 50 μs/Byte
- Hardware Data Protection
- DATA Polling for End of Program Detection
- Low Power Dissipation
 - 50 mA Active Current
 - 100 µA CMOS Standby Current
- Typical 10,000 Write Cycles

Description

The AT49F040 is a 5-volt-only in-system Flash Memory. Its 4 megabits of memory is organized as 524,288 words by 8 bits. Manufactured with Atmel's advanced nonvolatile CMOS technology, the device offers access times to 55 ns with power dissipation of just 275 mW over the commercial temperature range. When the device is deselected, the CMOS standby current is less than 100 μ A.

The device contains a user-enabled "boot block" protection feature. The AT49F040 locates the boot block at lowest order addresses ("bottom boot").

(continued)

Pin Configurations

Pin Name	Function
A0 - A18	Addresses
CE	Chip Enable
ŌĒ	Output Enable
WE	Write Enable
I/O0 - I/O7	Data Inputs/Outputs

DIP Top View

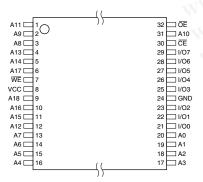
勝 特 力 材 料 886-3-5753170 胜特力电子(上海) 86-21-54151736

胜特力电子(深圳) 86-755-83298787

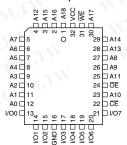
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1/1		\bigcirc	- 1	
A18 □	1		32	□ vcc
A16 🗆	2		31	□ WE
A15 🗆	3		30	□ A17
A12 🗆	4		29	□ A14
A7 □	5		28	□ A13
A6 🗆	6		27	□ A8
A5 🗆	7 <		26	□ A9
A4 🗆	8		25	A11
A3 🗆	9		24	D OE
A2 🗆	10		23	A10
A1 🗆	11		22	CE
A0 □	12		21	1/07
I/O0 [13		20	1/06
I/O1 [14		19	1/05
I/O2 [15		18	1/04
GND □	16		17	1/03
* I				TTV

TSOP Top View Type 1



PLCC Top View





4-megabit (512K x 8) 5-volt Only Flash Memory

AT49F040

Rev. 0998D-03/01





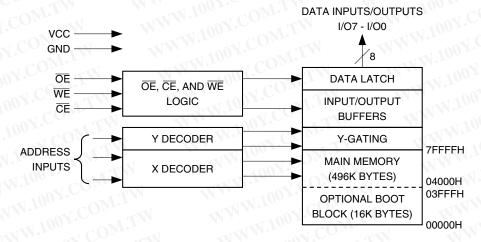
勝 特 力 材 料 886-3-5753170 胜特力电子(上海) 86-21-54151736 胜特力电子(深圳) 86-755-83298787 Http://www.100y.com.tw

To allow for simple in-system reprogrammability, the AT49F040 does not require high input voltages for programming. Five-volt-only commands determine the read and programming operation of the device. Reading data out of the device is similar to reading from an EPROM. Reprogramming the AT49F040 is performed by erasing the entire 4 megabits of memory and then programming on a byte-by-byte basis. The byte programming time is a fast 50 µs. The end of a program cycle can be optionally detected by the DATA polling feature. Once the end of a

byte program cycle has been detected, a new access for a read or program can begin. The typical number of program and erase cycles is in excess of 10,000 cycles.

The optional 16K bytes boot block section includes a reprogramming write lock out feature to provide data integrity. The boot sector is designed to contain user secure code, and when the feature is enabled, the boot sector is permanently protected from being reprogrammed.

Block Diagram



Device Operation

READ: The AT49F040 is accessed like an EPROM. When $\overline{\text{CE}}$ and $\overline{\text{OE}}$ are low and $\overline{\text{WE}}$ is high, the data stored at the memory location determined by the address pins is asserted on the outputs. The outputs are put in the high impedance state whenever $\overline{\text{CE}}$ or $\overline{\text{OE}}$ is high. This dual-line control gives designers flexibility in preventing bus contention.

ERASURE: Before a byte can be reprogrammed, the 512K bytes memory array (or 496K bytes if the boot block featured is used) must be erased. The erased state of the memory bits is a logical "1". The entire device can be erased at one time by using a 6-byte software code. The software chip erase code consists of 6-byte load commands to specific address locations with a specific data pattern (please refer to the Chip Erase Cycle Waveforms).

After the software chip erase has been initiated, the device will internally time the erase operation so that no external clocks are required. The maximum time needed to erase the whole chip is $t_{\rm EC}$. If the boot block lockout feature has been enabled, the data in the boot sector will not be erased.

BYTE PROGRAMMING: Once the memory array is erased, the device is programmed (to a logical "0") on a byte-by-byte basis. Please note that a data "0" cannot be

programmed back to a "1"; only erase operations can convert "0"s to "1"s. Programming is accomplished via the internal device command register and is a 4 bus cycle operation (please refer to the Command Definitions table). The device will automatically generate the required internal program pulses.

The program cycle has addresses latched on the falling edge of \overline{WE} or \overline{CE} , whichever occurs last, and the data latched on the rising edge of \overline{WE} or \overline{CE} , whichever occurs first. Programming is completed after the specified t_{BP} cycle time. The \overline{DATA} polling feature may also be used to indicate the end of a program cycle.

BOOT BLOCK PROGRAMMING LOCKOUT: The device has one designated block that has a programming lockout feature. This feature prevents programming of data in the designated block once the feature has been enabled. The size of the block is 16K bytes. This block, referred to as the boot block, can contain secure code that is used to bring up the system. Enabling the lockout feature will allow the boot code to stay in the device while data in the rest of the device is updated. This feature does not have to be activated; the boot block's usage as a write protected region is optional to the user. The address range of the boot block is 00000H to 03FFFH.

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AT49F040

Once the feature is enabled, the data in the boot block can no longer be erased or programmed. Data in the main memory block can still be changed through the regular programming method. To activate the lockout feature, a series of six program commands to specific addresses with specific data must be performed. Please refer to the Command Definitions table.

BOOT BLOCK LOCKOUT DETECTION: A software method is available to determine if programming of the boot block section is locked out. When the device is in the software product identification mode (see Software Product Identification Entry and Exit sections) a read from address location 00002H will show if programming the boot block is locked out. If the data on I/O0 is low, the boot block can be programmed; if the data on I/O0 is high, the program lock-out feature has been activated and the block cannot be programmed. The software product identification code should be used to return to standard operation.

PRODUCT IDENTIFICATION: The product identification mode identifies the device and manufacturer as Atmel. It may be accessed by hardware or software operation. The hardware operation mode can be used by an external programmer to identify the correct programming algorithm for the Atmel product.

For details, see Operating Modes (for hardware operation) or Software Product Identification. The manufacturer and device code is the same for both modes.

DATA POLLING: The AT49F040 features DATA polling to indicate the end of a program cycle. During a program cycle an attempted read of the last byte loaded will result in the complement of the loaded data on I/O7. Once the program cycle has been completed, true data is valid on all outputs and the next cycle may begin. DATA polling may begin at any time during the program cycle.

TOGGLE BIT: In addition to DATA polling the AT49F040 provides another method for determining the end of a program or erase cycle. During a program or erase operation, successive attempts to read data from the device will result in I/O6 toggling between one and zero. Once the program cycle has completed, I/O6 will stop toggling and valid data will be read. Examining the toggle bit may begin at any time during a program cycle.

HARDWARE DATA PROTECTION: Hardware features protect against inadvertent programs to the AT49F040 in the following ways: (a) V_{CC} sense: if V_{CC} is below 3.8V (typical), the program function is inhibited. (b) Program inhibit: holding any one of \overline{OE} low, \overline{CE} high or \overline{WE} high inhibits program cycles. (c) Noise filter: pulses of less than 15 ns (typical) on the \overline{WE} or \overline{CE} inputs will not initiate a program cycle.



Command Definition (in Hex)

Command Sequence	Command	Bus	1st l Cy	1.0	2nd Cyc		3rd Cy	Bus cle	W . JE	Bus cle	5th Cy			Bus cle
	Cycles	Addr	Data	Addr	Data	Addr	Data	Addr	Data	Addr	Data	Addr	Data	
Read	_N 1	Addr	D _{OUT}	ov.CO	Mr.	N	W	MM^{*}	· NOV.	CO_{Nr}	WT			
Chip Erase	6	5555	AA	2AAA	55	5555	80	5555	AA	2AAA	55	5555	10	
Byte Program	4	5555	AA	2AAA	55	5555	A0	Addr	D _{IN}	V.COD	T. T.			
Boot Block Lockout ⁽¹⁾	6	5555	AA	2AAA	55	5555	80	5555	AA	2AAA	55	5555	40	
Product ID Entry	3	5555	AA	2AAA	55	5555	90	-11	M.71	AT C	OM_{r_p}	a XV		
Product ID Exit ⁽²⁾	3	5555	AA	2AAA	55	5555	F0	- Au	WW.	00 2.	OM.	-XXI		
Product ID Exit ⁽²⁾	01.1	XXXX	F0	M.10	Dr.	$\sigma_{M,T}$	N	77		700 .	COM	I. I.		

Notes: 1. The 16K byte boot sector has the address range 00000H to 03FFFH.

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2. Either one of the Product ID exit commands can be used.

Absolute Maximum Ratings*

Temperature Under Bias	55°C to +125°C
Storage Temperature	65°C to +150°C
All Input Voltages (including NC Pins) with Respect to Ground	0.6V to +6.25V
All Output Voltages with Respect to Ground	0.6V to V _{CC} + 0.6V
Voltage on OE with Respect to Ground	0.6V to +13.5V

*NOTICE:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

AT49F040

DC and AC Operating Range

		AT49F040-55	AT49F040-70	AT49F040-90	AT49F040-12	
Operating	Com.	0°C - 70°C	0°C - 70°C	0°C - 70°C	0°C - 70°C	
Temperature (Case)	Ind.	-40°C - 85°C	-40°C - 85°C	-40°C - 85°C	-40°C - 85°C	
V _{CC} Power Supply	W WY	5V ± 10%	5V ± 10%	5V ± 10%	5V ± 10%	

Operating Modes

Mode	CE	ŌĒ	WE	Ai	1/0
Read	V _{IL}	VIL	V _{IH}	Ai NWW.100	D _{OUT}
Program ⁽²⁾	V _{IL}	V _{IH}	V _{IL}	OM. Ai	D _{IN}
Standby/Write Inhibit	V _{IH}	X ⁽¹⁾	X X	COM:11 X WWW.100	High Z
D WWW 100Y.Co	X	Х	V _{IH}	COM.TW	CONLI
Program Inhibit	X	V _{IL}	x 00	COM.TW WW.	OO TOMITY
Output Disable	X	V _{IH}	X	N.CO. MIN	High Z
Product Identification	ON	N	VWW.	OY.CO.TTW WWW	100Y.COMITW
MMM.100X	COM'I	N	WWW.	A1 - A18 = V _{IL} , A9 = V _H , ⁽³⁾ A0 = V _{IL}	Manufacturer Code ⁽⁴⁾
Hardware	V.COM	V _{IL}	V _{IH}	A1 - A18 = V _{IL} , A9 = V _H , ⁽³⁾ A0 = V _{IH}	Device Code ⁽⁴⁾
0 ((5)	ON CON		WW	A0 = V _{IL} , A1 - A18 = V _{IL}	Manufacturer Code ⁽⁴⁾
Software ⁽⁵⁾		MI		$A0 = V_{IH}, A1 - A18 = V_{IL}$	Device Code ⁽⁴⁾

WWW.100Y.COM.TW 5. See details under Software Product Identification Entry/Exit.

haracteristics

DC Characteristics

Symbol	Parameter	Condition	MMM. 100X	Min	Max	Units
I _{LI}	Input Load Current	V _{IN} = 0V to V _{CC}	MAN.	I.COM.	10	μΑ
I _{LO}	Output Leakage Current	$V_{I/O} = 0V \text{ to } V_{CC}$	MMM	Y.COM	N 10	μА
	V 0. II 0 10100	OF VCO ON AND AND AND AND AND AND AND AND AND AN	Com.	ON.COM.	100	μА
SB1	V _{CC} Standby Current CMOS	$\overline{\text{CE}} = V_{\text{CC}} - 0.3V \text{ to } V_{\text{CC}}$	Ind.	COM	300	μA
SB2	V _{CC} Standby Current TTL	$\overline{\text{CE}}$ = 2.0V to V _{CC}	WW.	Ion COL	3	mA
cc ⁽¹⁾	V _{CC} Active Current	f = 5 MHz; I _{OUT} = 0 mA	W. Tana	100,1	50	mA
V _{IL}	Input Low Voltage	TI 100Y. COM.TW			0.8	V
V _{IH}	Input High Voltage	1 100Y. OM.TW		2.0		V
V _{OL}	Output Low Voltage	I _{OL} = 2.1 mA			0.45	V
/ _{OH1}	Output High Voltage	I _{OH} = -400 μA		2.4		V
V _{OH2}	Output High Voltage CMOS	$I_{OH} = -100 \mu A; V_{CC} = 4.5 V$		4.2		V

1. In the erase mode, I_{CC} is 90 mA. Note:



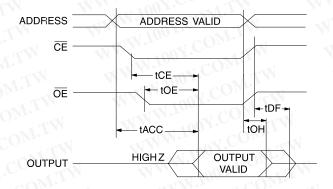


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AC Read Characteristics

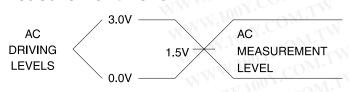
	AT49F040-55 AT49F040-70		AT49F040-90		AT49F040-12					
Symbol	Parameter	Min	Max	Min	Max	Min	Max	Min	Max	Units
t _{ACC}	Address to Output Delay	10 X.C.	55		70	W.100 Y	90	TW	120	ns
t _{CE} ⁽¹⁾	CE to Output Delay	1001.C	55	N	70	100	90	W.T.W	120	ns
t _{OE} ⁽²⁾	OE to Output Delay	0	30	0	35	0	40	0	50	ns
t _{DF} ⁽³⁾⁽⁴⁾	CE or OE to Output Float	00	25	0	25	0	25	0	30	ns
t _{OH}	Output Hold from OE, CE or Address, whichever occurred first	0.00	Y.CO	0		0	100 X.	CO01.7	TW	ns

AC Read Waveforms⁽¹⁾⁽²⁾⁽³⁾⁽⁴⁾

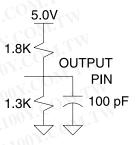


- Notes: 1. $\overline{\text{CE}}$ may be delayed up to t_{ACC} t_{CE} after the address transition without impact on t_{ACC} .
 - 2. $\overline{\text{OE}}$ may be delayed up to t_{CE} t_{OE} after the falling edge of $\overline{\text{CE}}$ without impact on t_{CE} or by t_{ACC} t_{OE} after an address change without impact on t_{ACC} .
 - 3. t_{DF} is specified from \overline{OE} or \overline{CE} whichever occurs first ($C_L = 5 \text{ pF}$).
 - 4. This parameter is characterized and is not 100% tested.

Input Test Waveforms and Measurement Level



Output Test Load



Pin Capacitance

 $f = 1 \text{ MHz}, T = 25^{\circ}C^{(1)}$

 t_{R} , t_{F} < 5 ns

Symbol	ы Тур Мах		Units	Conditions
C _{IN}	4	6	pF	$V_{IN} = 0V$
C _{OUT}	8	12	pF	$V_{OUT} = 0V$

Note: 1. This parameter is characterized and is not 100% tested.

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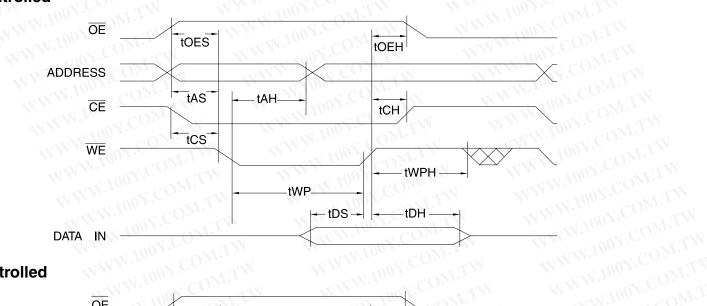
AT49F040

AC Byte Load Characteristics

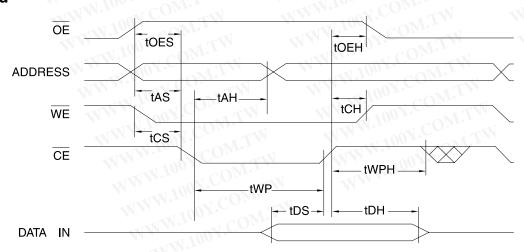
Symbol	Parameter	Min	Max	Units
t _{AH}	Address Hold Time	50	COMITW	ns
t _{cs}	Chip Select Set-up Time	0 100	COMITW	ns
t _{CH}	Chip Select Hold Time	0	OX.COM.TW	ns
t _{WP}	Write Pulse Width (WE or CE)	90	ONITH	ns
t _{DS}	Data Set-up Time	50	100Y.COM.T	ns
t _{DH} , t _{OEH}	Data, $\overline{\text{OE}}$ Hold Time	0	1 100X.COM.T	ns
t _{WPH}	Write Pulse Width High	90	11007.CO.	ns

AC Byte Load Waveforms

WE Controlled



CE Controlled





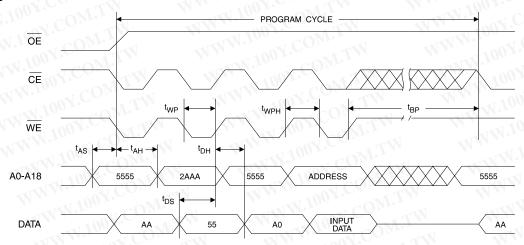


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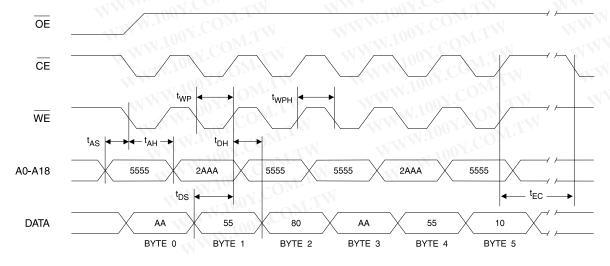
Program Cycle Characteristics

Symbol	Parameter	Min	Тур	Max	Units
t _{BP}	Byte Programming Time	10	10	50	μs
t _{AS}	Address Setup Time	0	ON.	TW	ns
t _{AH}	Address Hold Time	50	1001.001	I.TW	ns
t _{DS}	Data Setup Time	50	1007.00	M.T.W	ns
t _{DH}	Data Hold Time	0	x 1007.C	OM.TW	ns
t _{WP}	Write Pulse Width	90	100Y.C	WILMO	ns
t _{WPH}	Write Pulse Width High	90	100Y.	ON.TV	ns
t _{EC}	Erase Cycle Time	W	100	10	seconds

Program Cycle Waveforms



Chip Erase Cycle Waveforms



Note: \overline{OE} must be high only when \overline{WE} and \overline{CE} are both low.

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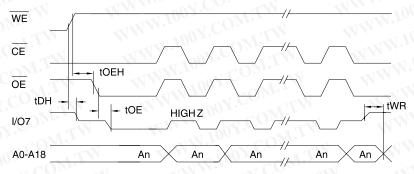
Data Polling Characteristics(1)

Symbol	Parameter	Min	Тур	Max	Units
t _{DH}	Data Hold Time	10	COM	1	ns
t _{OEH}	OE Hold Time	10	NOD.	TW	ns
t _{OE}	$\overline{\sf OE}$ to Output Delay ⁽²⁾	MAN	1007.00	N.T.W	ns
t _{WR}	Write Recovery Time	0	100Y.C	M.TW	ns

Notes: 1. These parameters are characterized and not 100% tested.

2. See t_{OE} spec in AC Read Characteristics.

Data Polling Waveforms



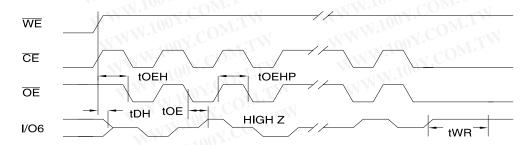
Toggle Bit Characteristics⁽¹⁾

Symbol	Parameter	WWW.LOOY	C Min	Тур	Max	Units
t _{DH}	Data Hold Time	MMMino	C 10	N	WWW	Cns
t _{OEH}	OE Hold Time	M. Ino	10	CV	MMMT	ns
t _{OE}	OE to Output Delay ⁽²⁾	WW.10	COM.		WWW.	ns
t _{OEHP}	OE High Pulse	W.1	150	1.	WWW	ns
t _{WR}	Write Recovery Time	N V	0000	1.17	W Take V	ns

Notes: 1. These parameters are characterized and not 100% tested.

2. See t_{OE} spec in AC Read Characteristics.

Toggle Bit Waveforms⁽¹⁾⁽²⁾⁽³⁾



Notes: 1. Toggling either \overline{OE} or \overline{CE} or both \overline{OE} and \overline{CE} will operate toggle bit. The t_{OEHP} specification must be met by the toggling input(s).

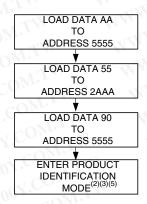
- 2. Beginning and ending state of I/O6 will vary.
- 3. Any address location may be used but the address should not vary.



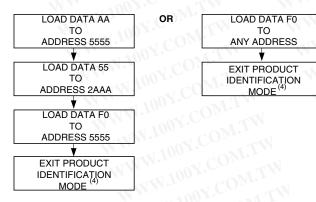


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Software Product Identification Entry⁽¹⁾



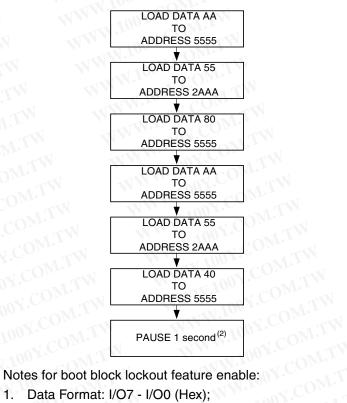
Software Product Identification Exit⁽¹⁾



Notes for software product identification:

- Data Format: I/O7 I/O0 (Hex); Address Format: A14 - A0 (Hex).
- 2. A1 A18 = V_{II} . Manufacture Code is read for $A0 = V_{II}$; Device Code is read for $A0 = V_{IH}$.
- The device does not remain in identification mode if powered down.
- The device returns to standard operation mode. WWW.100Y.COM.
- Manufacturer Code: 1FH 5. Device Code: 13H

Boot Block Lockout Feature Enable Algorithm⁽¹⁾



- Address Format: A14 A0 (Hex).
- WWW.100Y.COM.TW Boot block lockout feature enabled. WWW.100Y.COM.TW

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AT49F040

AT49F040 Ordering Information

t _{ACC} (ns)	I _{CC} (mA)		N.1001. COW.1	WW.100 2 CO	VI. I
	Active	Standby	Ordering Code	Package	Operation Range
55	50	0.1	AT49F040-55JC AT49F040-55PC AT49F040-55TC	32J 32P6 32T	Commercial (0° to 70°C)
	100X.COM	0.3	AT49F040-55JI AT49F040-55PI AT49F040-55TI	32J 32P6 32T	Industrial (-40° to 85°C)
70	50	0.1 0 M.T.W	AT49F040-70JC AT49F040-70PC AT49F040-70TC	32J 32P6 32T	Commercial (0° to 70°C)
	MM.100X	0.3	AT49F040-70JI AT49F040-70PI AT49F040-70TI	32J 32P6 32T	Industrial (-40° to 85°C)
90	50	0.1	AT49F040-90JC AT49F040-90PC AT49F040-90TC	32J 32P6 32T	Commercial (0° to 70°C)
		0.3	AT49F040-90JI AT49F040-90PI AT49F040-90TI	32J 32P6 32T	Industrial (-40° to 85°C)
120	50	0.1	AT49F040-12JC AT49F040-12PC AT49F040-12TC	32J 32P6 32T	Commercial (0° to 70°C)
		0.3	AT49F040-12JI AT49F040-12PI AT49F040-12TI	32J 32P6 32T	Industrial (-40° to 85°C)

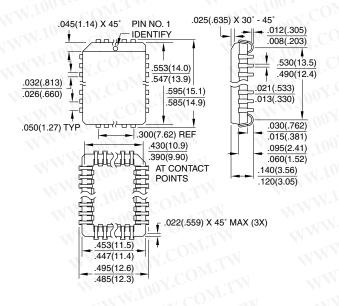
	Package Type	
32J	32-lead, Plastic, J-leaded Chip Carrier Package (PLCC)	
32P6	32-lead, 0.600" Wide, Plastic Dual Inline Package (PDIP)	
32T	32-lead, Thin Small Outline Package (TSOP)	



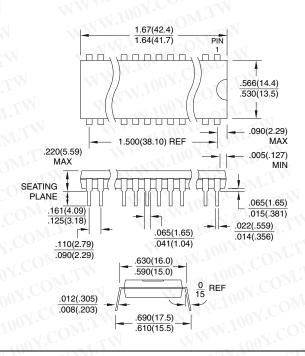
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Packaging Information

32J, 32-lead, Plastic J-leaded Chip Carrier (PLCC) Dimensions in Inches and (Millimeters) JEDEC STANDARD MS-016 AE

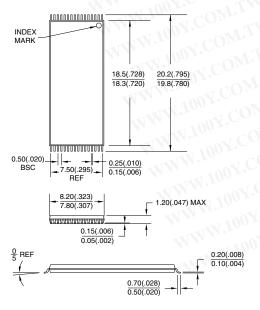


32P6, 32-lead, 0.600" Wide, Plastic Dual Inline Package (PDIP) Dimensions in Inches and (Millimeters)



32T, 32-lead, Plastic Thin Small Outline Package (TSOP)

Dimensions in Millimeters and (Inches)*
JEDEC OUTLINE MO-142 BA



*Controlling dimension: millimeters